

The revolutionary instrument for VLSI process improvement.

Stress Station

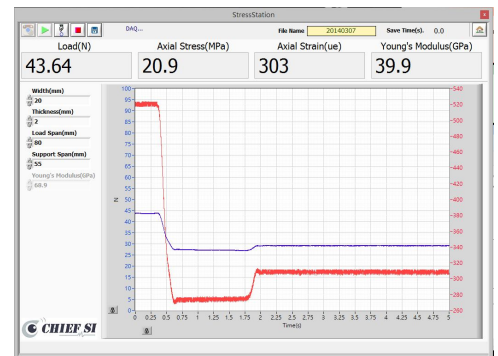


New measurement trend in wafer bending:

According to ITRS and Intel's CMOS process technology, stress technology has become one of the key technologies in advanced nano-meter CMOS process including 90nm and beyond. This stress station is capable of stress measurement in CMOS component and measurement of Piezo-resistance simultaneously. Similarly, this stress station is applicable to many research fields such as nano-wire, nano-tube, FinFET, GaAs component, SiGe channel component, Ge channel component, MEMS, LED, OLED, and PV.

Features :

- Direct measurement of sample's strain.
- Intuitive mechanism design in wafer bending jig for easy operation.
- Measurement results used in published international SCI journal paper.
- Adjustable single axial-direction stress provided by designed bending jig. (Including tension and compression)
- Augmentable to include I-V measurement and low frequency noise



Specifications :

Interface	USB 2.0	Max. sample size	80×100 mm
Measurement range	300 MPa ^{*1}	adjustable span range in applied force	95 mm
Stress resolution	0.05 MPa	Pitch in span adjustment	continuous adjustable
Stress type	tension or compression	Dimension (length×width×height)	240×210×195 mm
Young's modulus measure	Supported	Weight	5 Kg
Real-time stress calculation	Supported	Operating temperature	-20 ~ +60°C
Real-time displacement analysis	Supported (Optional)	Standard Accessory	Calibration sample, Software CD, USB cable,
Stress and applied force measure	Supported	Language	English
Max. applied force	100 N	PC Requirements	CPU:P4, HD:1GB, USB 2.0
Max. stroke of applied force	3 mm	Monitor Requirements	1280*800 resolution
Adjustment of applied force	simultaneously	O.S. Supported	Windows XP, WIN 7

*1: This range is calculated based on the Young's modulus of silicon wafer.



Tel : +886-3-5936268
 Mail : service01@chiefsi.com.tw
 Web : www.chiefsi.com.tw